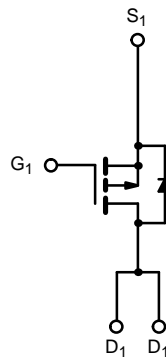
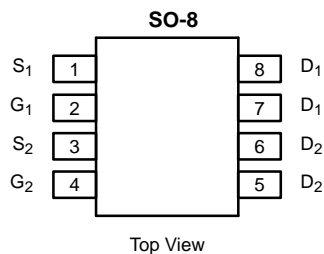


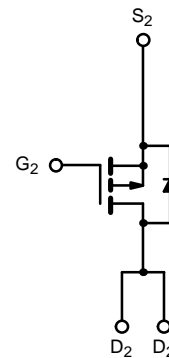
## Dual P-Channel 60-V (D-S), 175 °C MOSFET

**175 °C Rated**  
Maximum Junction Temperature  
**TrenchFET®**  
Power MOSFETs

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-60	0.120 @ $V_{GS} = -10$ V	$\pm 3.1$
	0.150 @ $V_{GS} = -4.5$ V	$\pm 2.8$



P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	-60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	$\pm 3.1$	A
	$T_A = 70^\circ\text{C}$		$\pm 2.6$	
Pulsed Drain Current		$I_{DM}$	$\pm 30$	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	-2.0	
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	2.4	W
	$T_A = 70^\circ\text{C}$		1.7	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Maximum Junction-to-Ambient <sup>a</sup>		$R_{thJA}$	62.5	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board,  $t \leq 10$  sec.



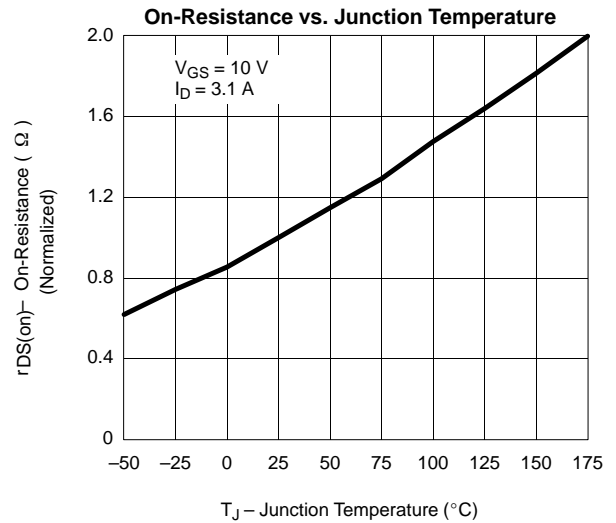
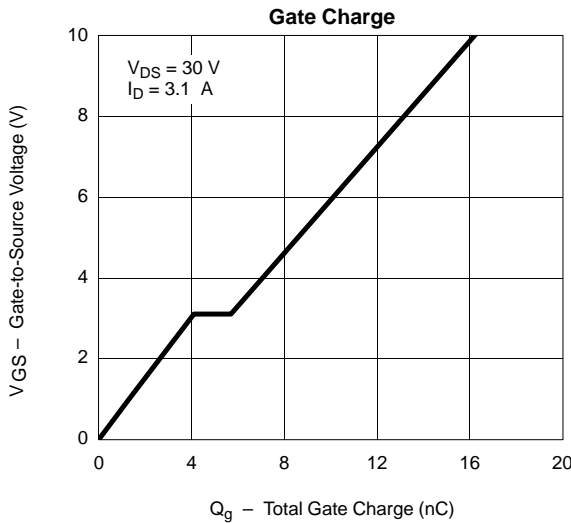
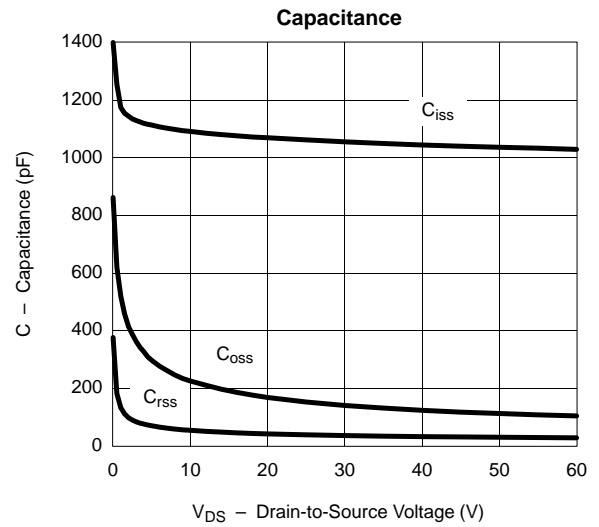
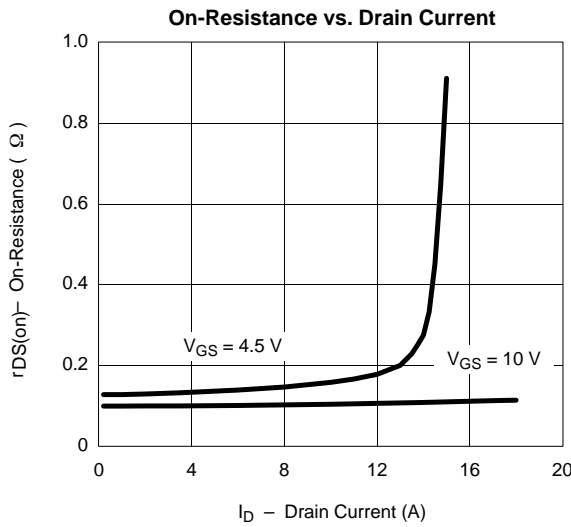
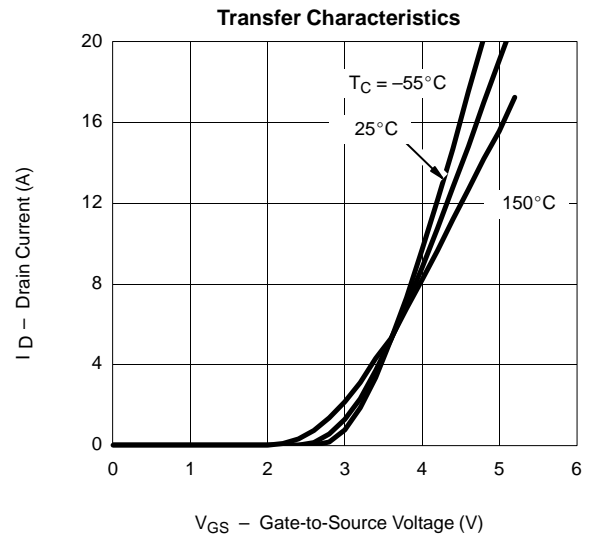
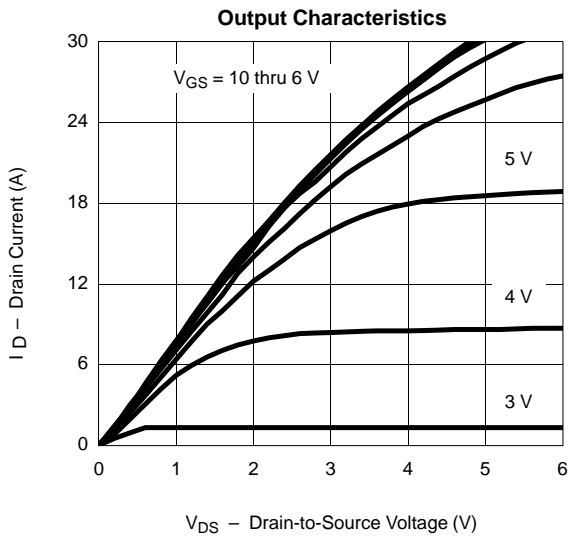
<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V			-2	μA
		V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			-25	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -10 V	-20			A
Drain-Source On-State Resistance <sup>b</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.1 A		0.100	0.120	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -2.8 A		0.125	0.150	
Forward Transconductance <sup>b</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -3.1 A		7.5		S
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = -2.0 A, V <sub>GS</sub> = 0 V		-0.8	-1.2	V
<b>Dynamic<sup>a</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.1 A		16	25	nC
Gate-Source Charge	Q <sub>gs</sub>			4		
Gate-Drain Charge	Q <sub>gd</sub>			1.6		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -30 V, R <sub>L</sub> = 30 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -10 V, R <sub>G</sub> = 6 Ω		8	15	ns
Rise Time	t <sub>r</sub>			10	20	
Turn-Off Delay Time	t <sub>d(off)</sub>			35	50	
Fall Time	t <sub>f</sub>			12	25	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -2.0 A, di/dt = 100 A/μs		60	90	

Notes

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**



**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

